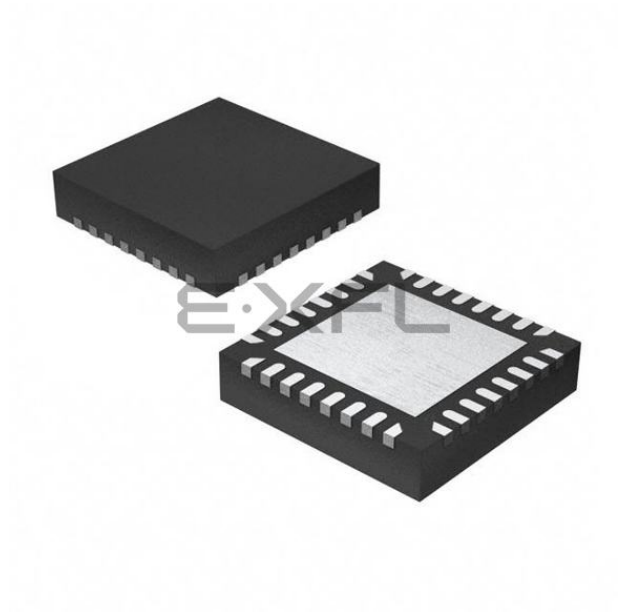
Lattice Semiconductor Corporation - LCMXO2-256HC-4SG32I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	32
Number of Logic Elements/Cells	256
Total RAM Bits	-
Number of I/O	21
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-256hc-4sg32i

Introduction

The MachXO2 family of ultra low power, instant-on, non-volatile PLDs has six devices with densities ranging from 256 to 6864 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic these devices feature Embedded Block RAM (EBR), Distributed RAM, User Flash Memory (UFM), Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support, advanced configuration support including dual-boot capability and hardened versions of commonly used functions such as SPI controller, I^2C controller and timer/counter. These features allow these devices to be used in low cost, high volume consumer and system applications.

The MachXO2 devices are designed on a 65 nm non-volatile low power process. The device architecture has several features such as programmable low swing differential I/Os and the ability to turn off I/O banks, on-chip PLLs and oscillators dynamically. These features help manage static and dynamic power consumption resulting in low static power for all members of the family.

The MachXO2 devices are available in two versions – ultra low power (ZE) and high performance (HC and HE) devices. The ultra low power devices are offered in three speed grades –1, –2 and –3, with –3 being the fastest. Similarly, the high-performance devices are offered in three speed grades: –4, –5 and –6, with –6 being the fastest. HC devices have an internal linear voltage regulator which supports external V_{CC} supply voltages of 3.3 V or 2.5 V. ZE and HE devices only accept 1.2 V as the external V_{CC} supply voltage. With the exception of power supply voltage all three types of devices (ZE, HC and HE) are functionally compatible and pin compatible with each other.

The MachXO2 PLDs are available in a broad range of advanced halogen-free packages ranging from the space saving 2.5 mm x 2.5 mm WLCSP to the 23 mm x 23 mm fpBGA. MachXO2 devices support density migration within the same package. Table 1-1 shows the LUT densities, package and I/O options, along with other key parameters.

The pre-engineered source synchronous logic implemented in the MachXO2 device family supports a broad range of interface standards, including LPDDR, DDR, DDR2 and 7:1 gearing for display I/Os.

The MachXO2 devices offer enhanced I/O features such as drive strength control, slew rate control, PCI compatibility, bus-keeper latches, pull-up resistors, pull-down resistors, open drain outputs and hot socketing. Pull-up, pull-down and bus-keeper features are controllable on a “per-pin” basis.

A user-programmable internal oscillator is included in MachXO2 devices. The clock output from this oscillator may be divided by the timer/counter for use as clock input in functions such as LED control, key-board scanner and similar state machines.

The MachXO2 devices also provide flexible, reliable and secure configuration from on-chip Flash memory. These devices can also configure themselves from external SPI Flash or be configured by an external master through the JTAG test access port or through the I^2C port. Additionally, MachXO2 devices support dual-boot capability (using external Flash memory) and remote field upgrade (TransFR) capability.

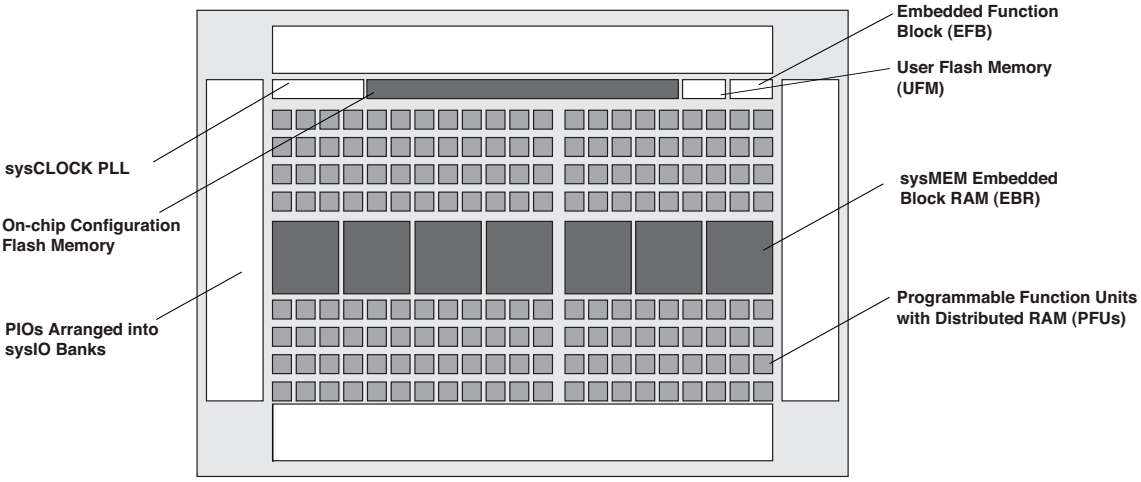
Lattice provides a variety of design tools that allow complex designs to be efficiently implemented using the MachXO2 family of devices. Popular logic synthesis tools provide synthesis library support for MachXO2. Lattice design tools use the synthesis tool output along with the user-specified preferences and constraints to place and route the design in the MachXO2 device. These tools extract the timing from the routing and back-annotate it into the design for timing verification.

Lattice provides many pre-engineered IP (Intellectual Property) LatticeCORE™ modules, including a number of reference designs licensed free of charge, optimized for the MachXO2 PLD family. By using these configurable soft core IP cores as standardized blocks, users are free to concentrate on the unique aspects of their design, increasing their productivity.

Architecture Overview

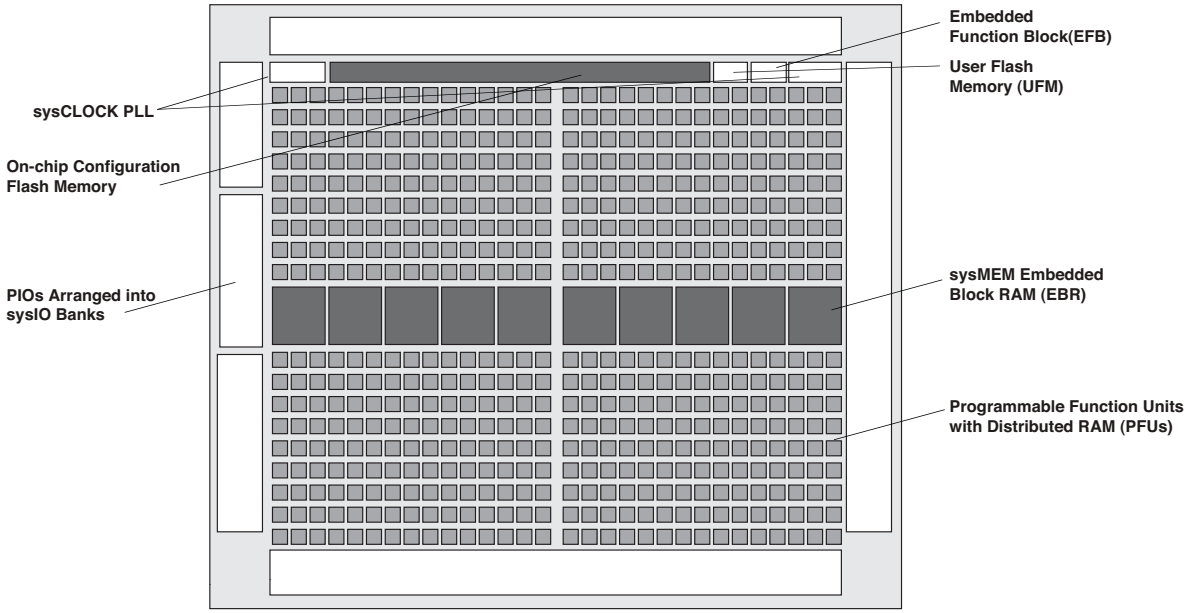
The MachXO2 family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). The larger logic density devices in this family have sysCLOCK™ PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.

Figure 2-1. Top View of the MachXO2-1200 Device



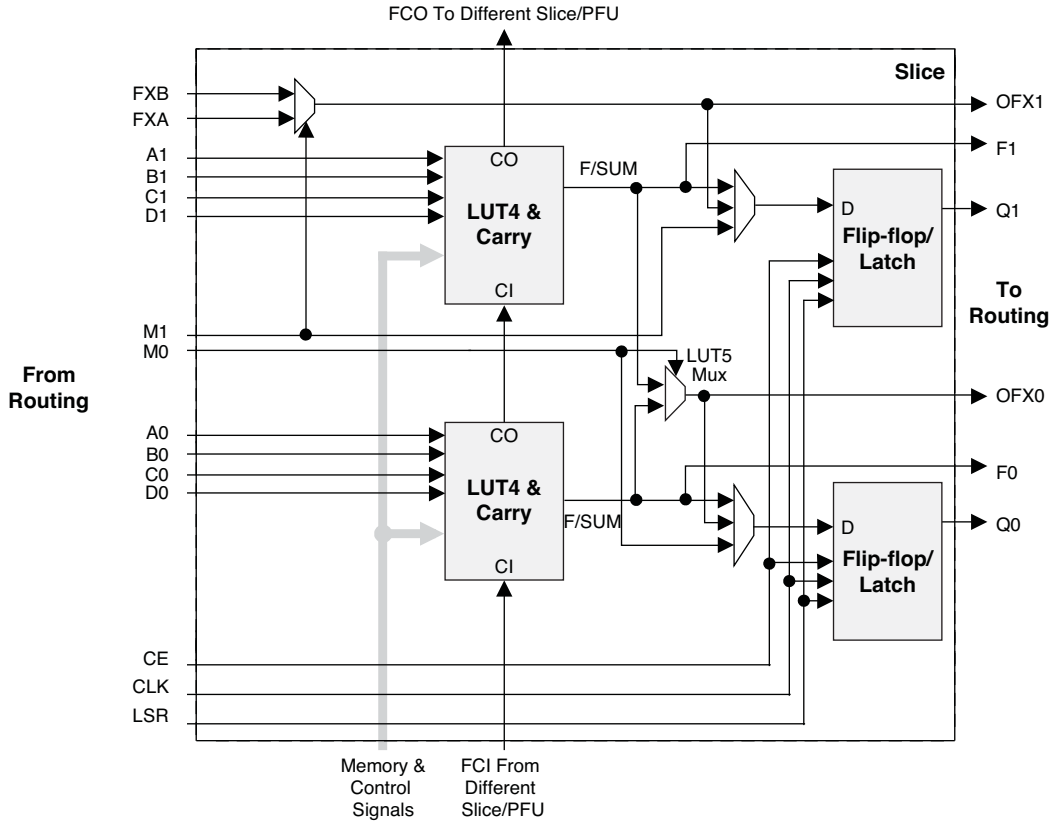
Note: MachXO2-256, and MachXO2-640/U are similar to MachXO2-1200. MachXO2-256 has a lower LUT count and no PLL or EBR blocks. MachXO2-640 has no PLL, a lower LUT count and two EBR blocks. MachXO2-640U has a lower LUT count, one PLL and seven EBR blocks.

Figure 2-2. Top View of the MachXO2-4000 Device



Note: MachXO2-1200U, MachXO2-2000/U and MachXO2-7000 are similar to MachXO2-4000. MachXO2-1200U and MachXO2-2000 have a lower LUT count, one PLL, and eight EBR blocks. MachXO2-2000U has a lower LUT count, two PLLs, and 10 EBR blocks. MachXO2-7000 has a higher LUT count, two PLLs, and 26 EBR blocks.

Figure 2-4. Slice Diagram



For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:

- WCK is CLK
- WRE is from LSR
- DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
- WAD [A:D] is a 4-bit address from slice 2 LUT input

Table 2-2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0/M1	Multi-purpose input
Input	Control signal	CE	Clock enable
Input	Control signal	LSR	Local set/reset
Input	Control signal	CLK	System clock
Input	Inter-PFU signal	FCIN	Fast carry in[1]
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8[2] MUX depending on the slice
Output	Inter-PFU signal	FCO	Fast carry out[1]

1. See Figure 2-3 for connection details.
2. Requires two PFUs.

ROM Mode

ROM mode uses the LUT logic; hence, slices 0-3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information on the RAM and ROM modes, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Routing

There are many resources provided in the MachXO2 devices to route signals individually or as buses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The inter-PFU connections are made with three different types of routing resources: x1 (spans two PFUs), x2 (spans three PFUs) and x6 (spans seven PFUs). The x1, x2, and x6 connections provide fast and efficient connections in the horizontal and vertical directions.

The design tools take the output of the synthesis tool and places and routes the design. Generally, the place and route tool is completely automatic, although an interactive routing editor is available to optimize the design.

Clock/Control Distribution Network

Each MachXO2 device has eight clock inputs (PCLK [T, C] [Banknum]_[2..0]) – three pins on the left side, two pins each on the bottom and top sides and one pin on the right side. These clock inputs drive the clock nets. These eight inputs can be differential or single-ended and may be used as general purpose I/O if they are not used to drive the clock nets. When using a single ended clock input, only the PCLKT input can drive the clock tree directly.

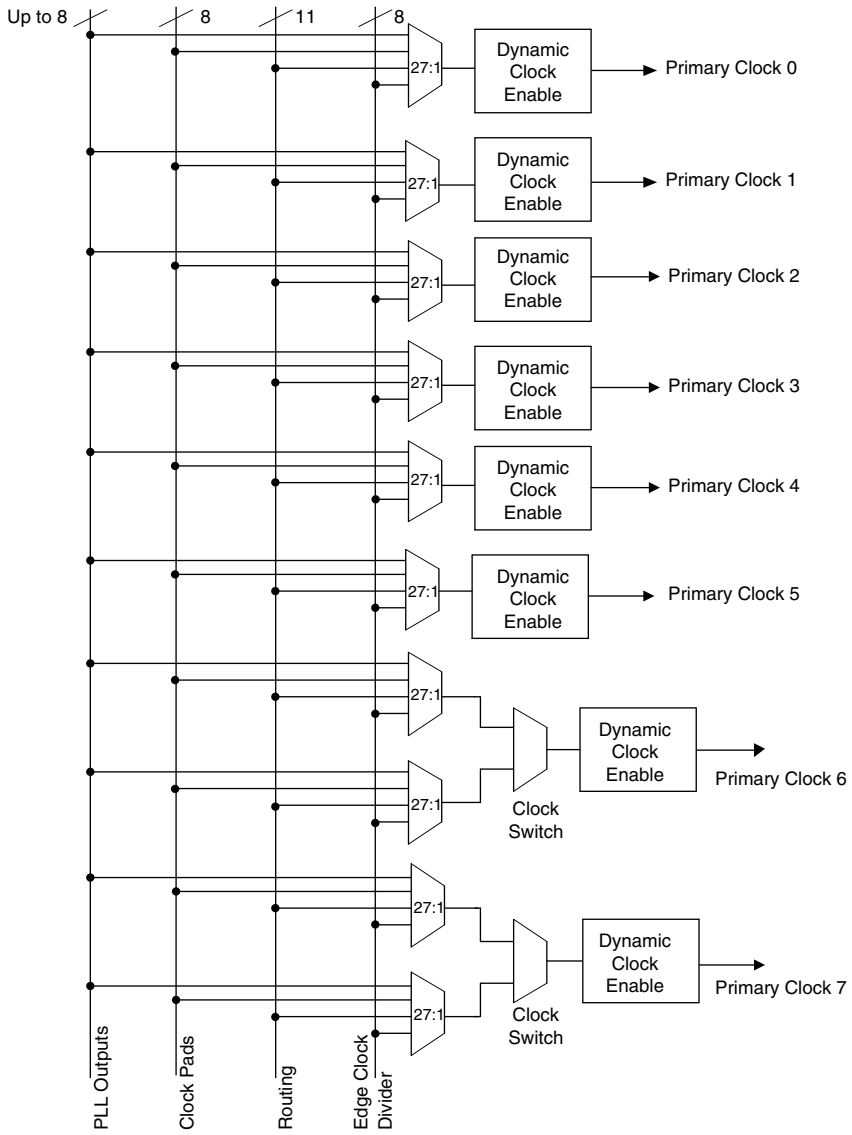
The MachXO2 architecture has three types of clocking resources: edge clocks, primary clocks and secondary high fanout nets. MachXO2-640U, MachXO2-1200/U and higher density devices have two edge clocks each on the top and bottom edges. Lower density devices have no edge clocks. Edge clocks are used to clock I/O registers and have low injection time and skew. Edge clock inputs are from PLL outputs, primary clock pads, edge clock bridge outputs and CIB sources.

The eight primary clock lines in the primary clock network drive throughout the entire device and can provide clocks for all resources within the device including PFUs, EBRs and PICs. In addition to the primary clock signals, MachXO2 devices also have eight secondary high fanout signals which can be used for global control signals, such as clock enables, synchronous or asynchronous clears, presets, output enables, etc. Internal logic can drive the global clock network for internally-generated global clocks and control signals.

The maximum frequency for the primary clock network is shown in the MachXO2 External Switching Characteristics table.

The primary clock signals for the MachXO2-256 and MachXO2-640 are generated from eight 17:1 muxes The available clock sources include eight I/O sources and 9 routing inputs. Primary clock signals for the MachXO2-640U, MachXO2-1200/U and larger devices are generated from eight 27:1 muxes The available clock sources include eight I/O sources, 11 routing inputs, eight clock divider inputs and up to eight sysCLOCK PLL outputs.

Figure 2-5. Primary Clocks for MachXO2 Devices



Primary clocks for MachXO2-640U, MachXO2-1200/U and larger devices.

Note: MachXO2-640 and smaller devices do not have inputs from the Edge Clock Divider or PLL and fewer routing inputs. These devices have 17:1 muxes instead of 27:1 muxes.

Eight secondary high fanout nets are generated from eight 8:1 muxes as shown in Figure 2-6. One of the eight inputs to the secondary high fanout net input mux comes from dual function clock pins and the remaining seven come from internal routing. The maximum frequency for the secondary clock network is shown in MachXO2 External Switching Characteristics table.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

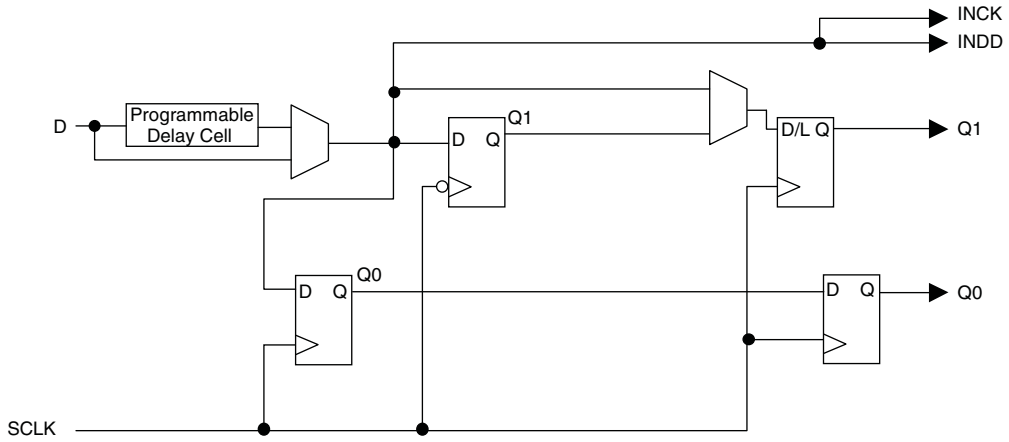
Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.

Figure 2-12. MachXO2 Input Register Block Diagram (PIO on Left, Top and Bottom Edges)



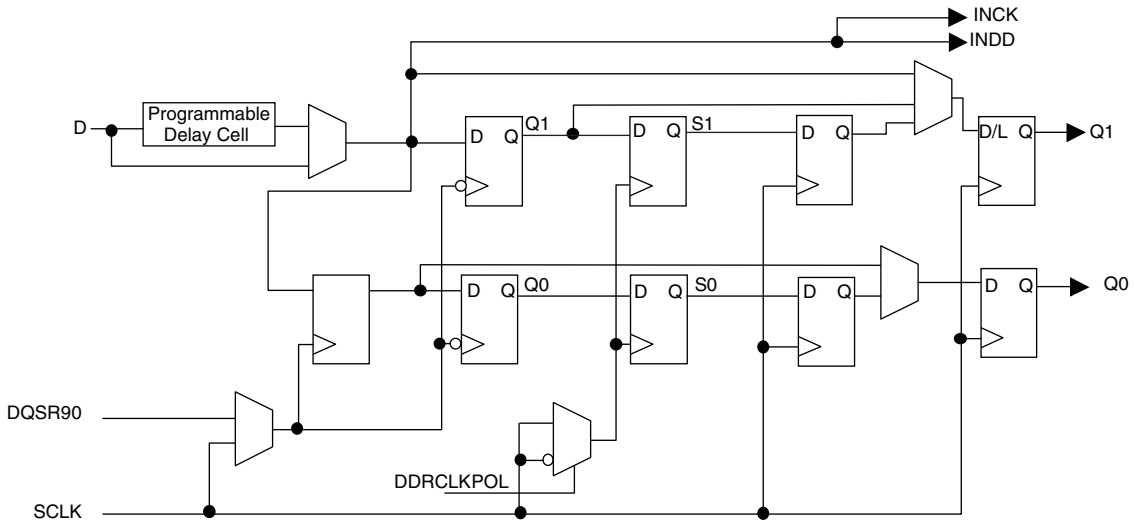
Right Edge

The input register block on the right edge is a superset of the same block on the top, bottom, and left edges. In addition to the modes described above, the input register block on the right edge also supports DDR memory mode.

In DDR memory mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (DQSR90) in the DDR Memory mode creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the DQS domain. The DQSR90 and DDRCLKPOL signals are generated in the DQS read-write block.

Figure 2-13. MachXO2 Input Register Block Diagram (PIO on Right Edge)



Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

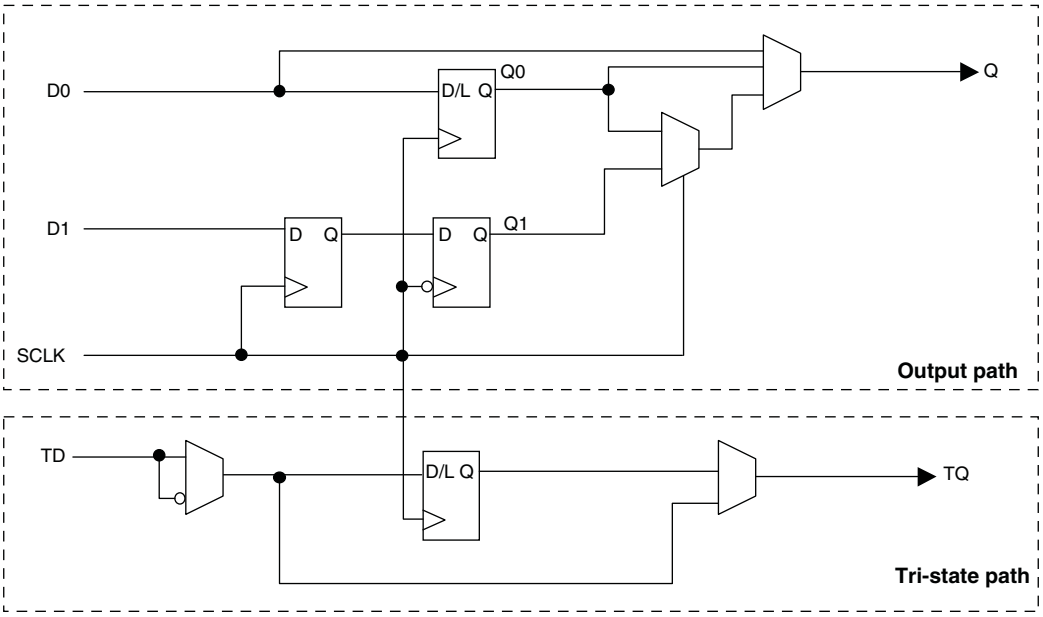
Left, Top, Bottom Edges

In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-14 shows the output register block on the left, top and bottom edges.

Figure 2-14. MachXO2 Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



Right Edge

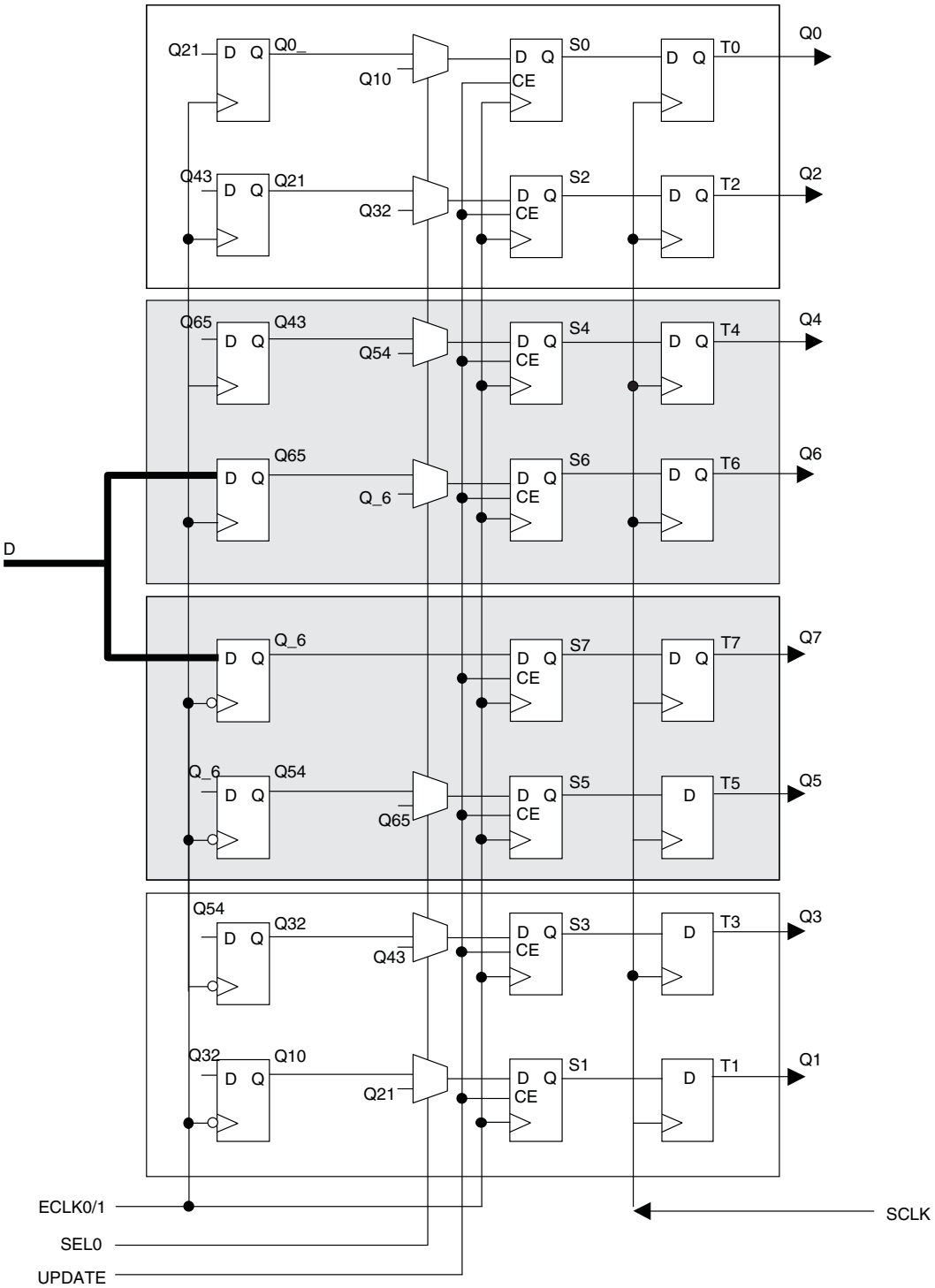
The output register block on the right edge is a superset of the output register on left, top and bottom edges of the device. In addition to supporting SDR and Generic DDR modes, the output register blocks for PIOs on the right edge include additional logic to support DDR-memory interfaces. Operation of this block is similar to that of the output register block on other edges.

In DDR memory mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the DQSW90 signal is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-15 shows the output register block on the right edge.

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-16 shows a block diagram of the input gearbox.

Figure 2-16. Input Gearbox



When implementing background programming of the on-chip Flash, care must be taken for the operation of the PLL. For devices that have two PLLs (XO2-2000U, -4000 and -7000), the system must put the RPLL (Right-side PLL) in reset state during the background Flash programming. More detailed description can be found in TN1204, MachXO2 Programming and Configuration Usage Guide.

Security and One-Time Programmable Mode (OTP)
For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO2 devices contain security bits that, when set, prevent the readback of the SRAM configuration and non-volatile Flash memory spaces. The device can be in one of two modes:

1. Unlocked – Readback of the SRAM configuration and non-volatile Flash memory spaces is allowed.

2. Permanently Locked – The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the Flash and SRAM OTP portions of the device. For more details, refer to TN1204, MachXO2 Programming and Configuration Usage Guide.

Dual Boot
MachXO2 devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the on-chip Flash. The golden image MUST reside in an external SPI Flash. For more details, refer to TN1204, MachXO2 Programming and Configuration Usage Guide.

Soft Error Detection
The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1206, MachXO2 Soft Error Detection Usage Guide.

TraceID

Each MachXO2 device contains a unique (per device), TraceID that can be used for tracking purposes or for IP security applications. The TraceID is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TraceID is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I^2C, or JTAG interfaces.

Density Shifting

The MachXO2 family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the MachXO2 migration files.

Power-On-Reset Voltage Levels[1, 2, 3, 4, 5]

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max.[1]	Units
$N_{PROGCYC}$	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/–1000	µA

1. Insensitive to sequence of V_{CC} and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO}.
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} –0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} –0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < V_{IN} < V_{CCIO}	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	-309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < V_{IN} < V_{CCIO}	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pF
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pF
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-to-low transition. For true LVDS output pins in MachXO2-640U, MachXO2-1200/U and larger devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1202, MachXO2 sysIO Usage Guide.

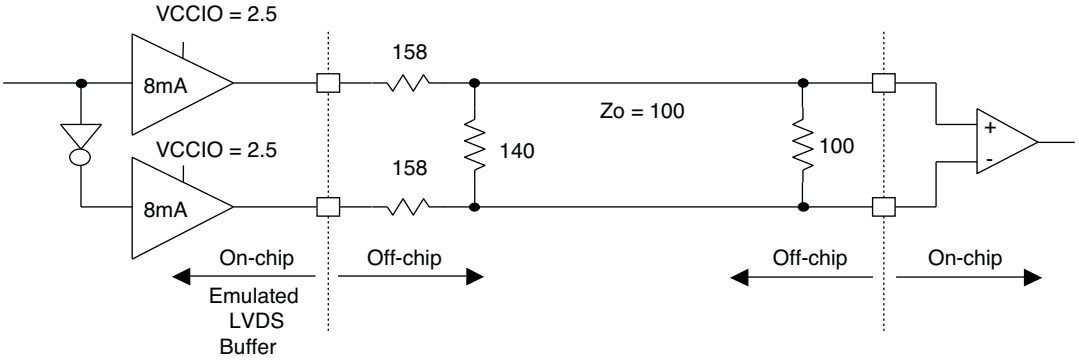
sysIO Single-Ended DC Electrical Characteristics[1, 2]

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max.[4] (mA)	I_{OH} Max.[4] (mA)
	Min. (V)[3]	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
							16	–16
							24	–24
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 2.5	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
							16	–16
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.8	–0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.5	–0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.2	–0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} – 0.4	4	–2
							8	–6
					0.2	V_{CCIO} – 0.2	0.1	–0.1
PCI	–0.3	$0.3V_{CCIO}$	$0.5V_{CCIO}$	3.6	$0.1V_{CCIO}$	$0.9V_{CCIO}$	1.5	–0.5
SSTL25 Class I	–0.3	V_{REF} – 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	8	8
SSTL25 Class II	–0.3	V_{REF} – 0.18	V_{REF} + 0.18	3.6	NA	NA	NA	NA
SSTL18 Class I	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.6	0.40	V_{CCIO} - 0.40	8	8
SSTL18 Class II	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.6	NA	NA	NA	NA
HSTL18 Class I	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	V_{CCIO} - 0.40	8	8
HSTL18 Class II	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS25R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

LVDS Emulation

MachXO2 devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)



Note: All resistors are ±1%.

Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	158	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

Typical Building Block Function Performance – ZE Devices[1]

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	–3 Timing	Units
Basic Functions		
16-bit decoder	13.9	ns
4:1 MUX	10.9	ns
16:1 MUX	12.0	ns

Register-to-Register Performance

Function	–3 Timing	Units
Basic Functions		
16:1 MUX	191	MHz
16-bit adder	134	MHz
16-bit counter	148	MHz
64-bit counter	77	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	90	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	214	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	0.434	—	0.535	—	0.630	—	ns
t_{HO}	Input Data Hold After ECLK		0.385	—	0.395	—	0.463	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Inputs – GDDR71_RX.ECLK.7.1[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.307	—	0.316	—	0.326	UI
t_{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides	—	0.850	—	0.910	—	0.970	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.850	—	0.910	—	0.970	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	70	—	58	—	49	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides	2.720	—	3.380	—	4.140	—	ns
t_{DVA}	Output Data Valid After CLK Output		2.720	—	3.380	—	4.140	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	70	—	58	—	49	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz

sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t_{PRGM}	PROGRAMN low pulse accept		55	—	ns
t_{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t_{INITL}	INITN low time	LCMXO2-256	—	30	µs
		LCMXO2-640	—	35	µs
		LCMXO2-640U/ LCMXO2-1200	—	55	µs
		LCMXO2-1200U/ LCMXO2-2000	—	70	µs
		LCMXO2-2000U/ LCMXO2-4000	—	105	µs
		LCMXO2-7000	—	130	µs
$t_{DPPINIT}$	PROGRAMN low to INITN low		—	150	ns
$t_{DPPDONE}$	PROGRAMN low to DONE low		—	150	ns
t_{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f_{MAX}	CCLK clock frequency		—	66	MHz
t_{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t_{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t_{STSU}	CCLK setup time		2	—	ns
t_{STH}	CCLK hold time		0	—	ns
t_{STCO}	CCLK falling edge to valid output		—	10	ns
t_{STOZ}	CCLK falling edge to valid disable		—	10	ns
t_{STOV}	CCLK falling edge to valid enable		—	10	ns
t_{SCS}	Chip select high time		25	—	ns
t_{SCSS}	Chip select setup time		3	—	ns
t_{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f_{MAX}	MCLK clock frequency		—	133	MHz
t_{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t_{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t_{STSU}	MCLK setup time		5	—	ns
t_{STH}	MCLK hold time		1	—	ns
t_{CSSPI}	INITN high to chip select low		100	200	ns
t_{MCLK}	INITN high to first MCLK edge		0.75	1	µs

Pinout Information Summary

	MachXO2-256					MachXO2-640			MachXO2-640U
	32 QFN[1]	48 QFN[3]	64 ucBGA	100 TQFP	132 csBGA	48 QFN[3]	100 TQFP	132 csBGA	144 TQFP
General Purpose I/O per Bank									
Bank 0	8	10	9	13	13	10	18	19	27
Bank 1	2	10	12	14	14	10	20	20	26
Bank 2	9	10	11	14	14	10	20	20	28
Bank 3	2	10	12	14	14	10	20	20	26
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Single Ended I/O	21	40	44	55	55	40	78	79	107
Differential I/O per Bank									
Bank 0	4	5	5	7	7	5	9	10	14
Bank 1	1	5	6	7	7	5	10	10	13
Bank 2	4	5	5	7	7	5	10	10	14
Bank 3	1	5	6	7	7	5	10	10	13
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
Total General Purpose Differential I/O	10	20	22	28	28	20	39	40	54
Dual Function I/O	22	25	27	29	29	25	29	29	33
High-speed Differential I/O									
Bank 0	0	0	0	0	0	0	0	0	7
Gearboxes									
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	0	0	0	0	0	0	0	0	7
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	0	0	0	0	0	0	0	0	7
DQS Groups									
Bank 1	0	0	0	0	0	0	0	0	2
VCCIO Pins									
Bank 0	2	2	2	2	2	2	2	2	3
Bank 1	1	1	2	2	2	1	2	2	3
Bank 2	2	2	2	2	2	2	2	2	3
Bank 3	1	1	2	2	2	1	2	2	3
Bank 4	0	0	0	0	0	0	0	0	0
Bank 5	0	0	0	0	0	0	0	0	0
VCC	2	2	2	2	2	2	2	2	4
GND[2]	2	1	8	8	8	1	8	10	12
NC	0	0	1	26	58	0	3	32	8
Reserved for Configuration	1	1	1	1	1	1	1	1	1
Total Count of Bonded Pins	32	49	64	100	132	49	100	132	144

1. Lattice recommends soldering the central thermal pad onto the top PCB ground for improved thermal resistance.
2. For 48 QFN package, exposed die pad is the device ground.
3. 48-pin QFN information is 'Advanced'.

High-Performance Commercial Grade Devices with Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256HC-4SG32C	256	2.5 V / 3.3 V	–4	Halogen-Free QFN	32	COM
LCMXO2-256HC-5SG32C	256	2.5 V / 3.3 V	–5	Halogen-Free QFN	32	COM
LCMXO2-256HC-6SG32C	256	2.5 V / 3.3 V	–6	Halogen-Free QFN	32	COM
LCMXO2-256HC-4SG48C	256	2.5 V / 3.3 V	–4	Halogen-Free QFN	48	COM
LCMXO2-256HC-5SG48C	256	2.5 V / 3.3 V	–5	Halogen-Free QFN	48	COM
LCMXO2-256HC-6SG48C	256	2.5 V / 3.3 V	–6	Halogen-Free QFN	48	COM
LCMXO2-256HC-4UMG64C	256	2.5 V / 3.3 V	–4	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-5UMG64C	256	2.5 V / 3.3 V	–5	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-6UMG64C	256	2.5 V / 3.3 V	–6	Halogen-Free ucBGA	64	COM
LCMXO2-256HC-4TG100C	256	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-256HC-5TG100C	256	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-256HC-6TG100C	256	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-256HC-4MG132C	256	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-256HC-5MG132C	256	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-256HC-6MG132C	256	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640HC-4SG48C	640	2.5 V / 3.3 V	–4	Halogen-Free QFN	48	COM
LCMXO2-640HC-5SG48C	640	2.5 V / 3.3 V	–5	Halogen-Free QFN	48	COM
LCMXO2-640HC-6SG48C	640	2.5 V / 3.3 V	–6	Halogen-Free QFN	48	COM
LCMXO2-640HC-4TG100C	640	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-640HC-5TG100C	640	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-640HC-6TG100C	640	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-640HC-4MG132C	640	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-640HC-5MG132C	640	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-640HC-6MG132C	640	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640UHC-4TG144C	640	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-640UHC-5TG144C	640	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-640UHC-6TG144C	640	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM